

## KSC2331

# Low Frequency Amplifier & Medium Speed Switching

- Complement to KSA931
- High Collector-Base Voltage : V<sub>CBO</sub>=80V
- Collector Current : I<sub>C</sub>=700mA
- Collector Dissipation : P<sub>C</sub>=1W



### 1. Emitter 2. Collector 3. Base

## **NPN Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	8	V
I <sub>C</sub>	Collector Current	700	mA
P <sub>C</sub>	Collector Power Dissipation	1	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>E</sub> =0	80			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	60			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E}=10\mu A, I_{C}=0$	8			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =60V, I <sub>E</sub> =0			0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =5V, $I_{C}$ =0			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE}$ =2V, $I_{C}$ =50mA	40		240	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		0.2	0.7	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		0.86	1.20	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA	30	50		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		8		pF

## **h**<sub>FE</sub> Classification

Classification	R	0	Y
h <sub>FE</sub>	40 ~ 80	70 ~ 140	120 ~ 240

## **Typical Characteristics**

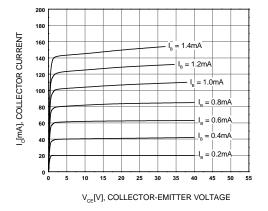


Figure 1. Static Characteristic

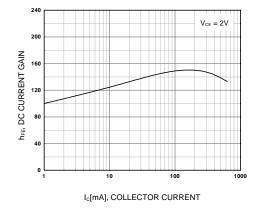


Figure 2. DC current Gain

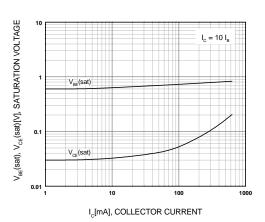


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

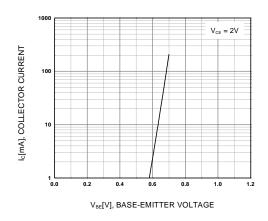


Figure 4. Base-Emitter On Voltage

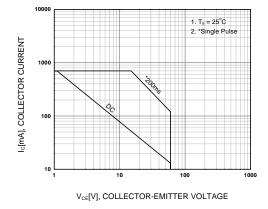


Figure 5. Safe Operating Area

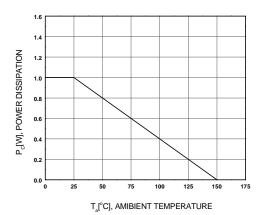
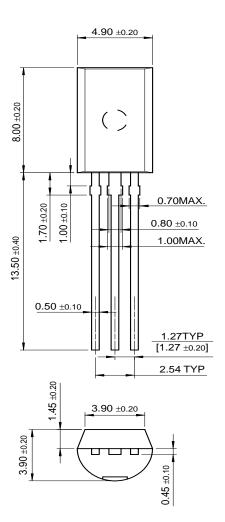


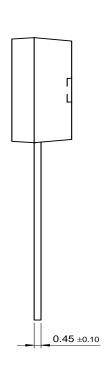
Figure 6. Power Derating

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## **Package Demensions**

## TO-92L





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**Switching** 

company

### Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSC2331OTA	Full Production	\$0.08	TO-92	3	TAPE REEL
KSC2331YTA	Full Production	\$0.08	TO-92	3	TAPE REEL
KSC2331YSHTA	Full Production	\$0.058	<u>TO-92</u>	3	TAPE REEL
KSC2331YBU	Full Production	\$0.08	TO-92	3	BULK
KSC2331OBU	Full Production	\$0.08	TO-92	3	BULK

<sup>\* 1,000</sup> piece Budgetary Pricing

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